WHAT IS CLAIMED IS:

A method for processing integrated circuit devices including a water
process comprising:
ng a chemical mechanical planarization process, the chemical mechanical
ncluding a discharge for process water, the process water being used to
emiconductor wafers;
ely discharging process water from the discharge;
ring the process water from the chemical mechanical planarization proces
nd .
ne discharged water in the facility process.
The method of claim 1 wherein the facility process includes a cooling
r.
The method of claim 1 wherein the discharge water is characterized by a
a about 6 to about 10.
The method of claim 1 wherein the discharge water is characterized by a
an about 2000 μ siemens per centimeter.
The method of claim 1 wherein the selectively discharging is provided
coupled to the discharge, the control valve being coupled to computer
The method of claim 1 wherein the discharge includes a plurality of lines,
coupled to one or more processing stations.
The method of claim 1 wherein the transferring to the facility process
to a collection tank before transferring the discharge water to the facility
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1	8. The method of claim 1 wherein the selectively discharging comprises
2	outputting a signal in response to process in computer software to open a value to release the
3	process water.
1	9. The method of claim 1 wherein the process water is ultra-pure water
2	having a resistivity of about 18 Mega-ohms.
1	10. The method of claim 1 wherein the transferring of the process water from
2	the chemical mechanical planarization process to a facility process occurs free from any
3	chemical treatment between the chemical mechanical planarization process and the facility
4	process.
1	11. A method for processing integrated circuit devices including a water
2	recycling process, the process comprising:
3	operating a chemical mechanical polishing process using an incoming stream of
4	ultra-pure water, the chemical mechanical polishing process including a discharge for used ultra-
5	pure water, the ultra-pure water being used to process one or more semiconductor wafers and
6	discharged through the discharge to form a facility water;
7	selectively discharging the facility water from the discharge of the chemical
8	mechanical polishing process and transferring the facility water from the discharge of the
9	chemical mechanical polishing process to a facility process, the transferring being free from any
10	chemical treatment of the discharged process water; and
11	using the discharged water in the facility process.
1	12. The method of claim 11 wherein selectively discharging is provided by a
2	valve coupled to the chemical mechanical planarization process.
1	13. The method of claim 11 wherein the ultra-pure water is characterized by a
2	resistance of about 18 mega-ohm.
1	14. The method of claim 13 wherein the ultra-pure water is substantially free

from particles greater than about 0.05 microns in dimension.

1	15. The method of claim 11 wherein the transferring the facility water from
2	the discharge of the chemical mechanical polishing process to a facility process includes storing
3	the facility water in a storage facility before use by the facility process.
1	16. The method of claim 15 wherein the facility process is selected from a
2	cooling process, a scrubbing process.
1 2	17. A system for chemical mechanical polishing, the system comprising: a plurality of processing stations, each of the processing stations being configured
3	to perform at least one processing operation;
4	a discharge line coupled to one or more of the processing stations to receive
5	discharge water;
6	a valve coupled to the discharge line to selectively output the discharge water for
7	use in a facility process; and
8	a drain line coupled to the discharge line for outputting the discharge water to a
9	drain.
1	18. The system of claim 17 further comprising a computer system coupled to
2	the valve, the computer system including one or more memories, the one or more memories
3	including a first code directed to actuate the value to output the discharge water for use in the
4	facility process.
1	19. The system of claim 17 wherein the discharge line comprises a plurality of
2	lines.
1	20. The system of claim 17 further comprising a source line for ultra-pure
2	water coupled to one or more of the processing stations, the ultra-pure water being discharge

water after being used by one or more of the processing stations.